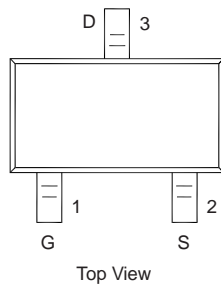


N-Channel 600 V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
600	80 at V _{GS} = 10 V	0.15

(SOT-23-3L)



FEATURES

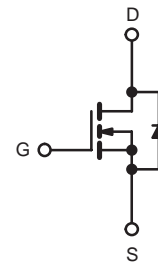
- DT-Trench Power MOSFET
- 100% R_g and UIS Tested

APPLICATIONS

- High efficient switched mode power supplies
- TV Power
- Adapter/charger



RoHS
COMPLIANT



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 175 °C) ^a	I _D	T _A = 25 °C	A
		T _A = 70 °C	
Pulsed Drain Current	I _{DM}	0.6	A
Avalanche Current	I _{AS}	0.12	
Peak diode recovery dv/dt	dv/dt	6	V/ns
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	W
		T _A = 70 °C	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	55	115	°C/W
	Steady State		38	85	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	12	28	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

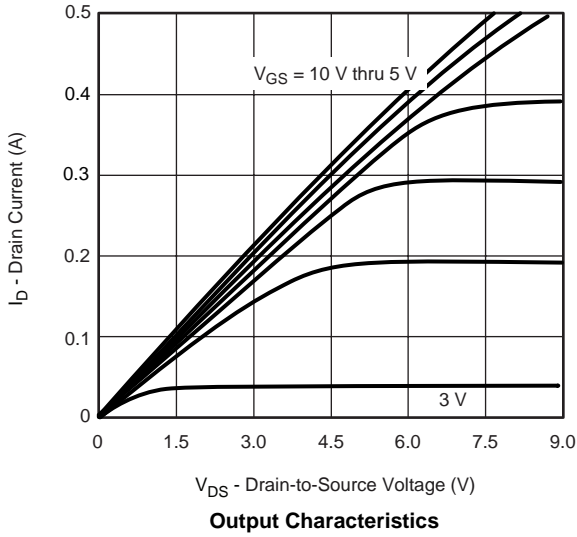
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	600			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		0.6		V/ $^\circ\text{C}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = -10\text{ V}$	19			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 0.02\text{ A}$		80	120	Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = 40\text{ V}, I_D = 0.02\text{ A}$		0.22		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 300\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		73		μF
Output Capacitance	C_{oss}			12		
Reverse Transfer Capacitance	C_{rss}			5		
Total Gate Charge	Q_g	$V_{DS} = 300\text{ V}, V_{GS} = 10\text{ V}, I_D = 0.02\text{ A}$		3.9		nC
Gate-Source Charge	Q_{gs}			0.28		
Gate-Drain Charge	Q_{gd}			2.6		
Gate Resistance	R_g	$f = 1\text{ MHz}$		6.5		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 300\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 0.02\text{ A}, V_{GS} = 10\text{ V}, R_g = 1\text{ }\Omega$		7		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(off)}$			18		
Fall Time	t_f			52		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			0.15	A
Pulse Diode Forward Current ^a	I_{SM}				0.6	
Body Diode Voltage	V_{SD}	$I_S = 0.15\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 0.15\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		152		ns
Body Diode Reverse Recovery Charge	Q_{rr}				165	

Notes:

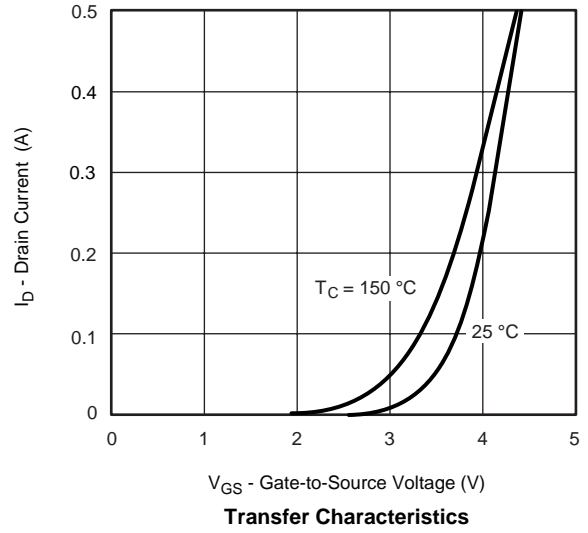
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

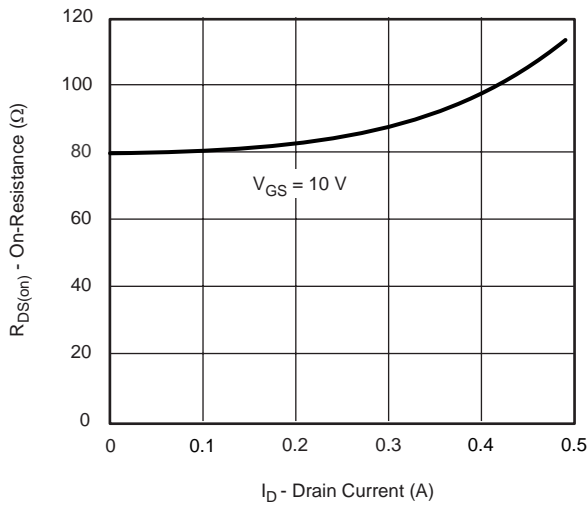
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



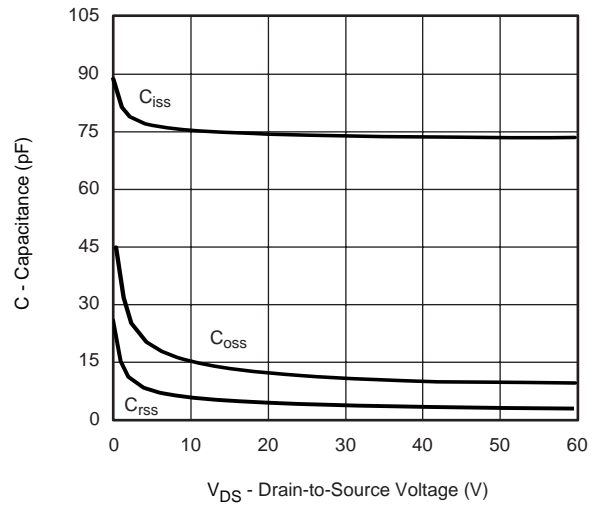
Output Characteristics



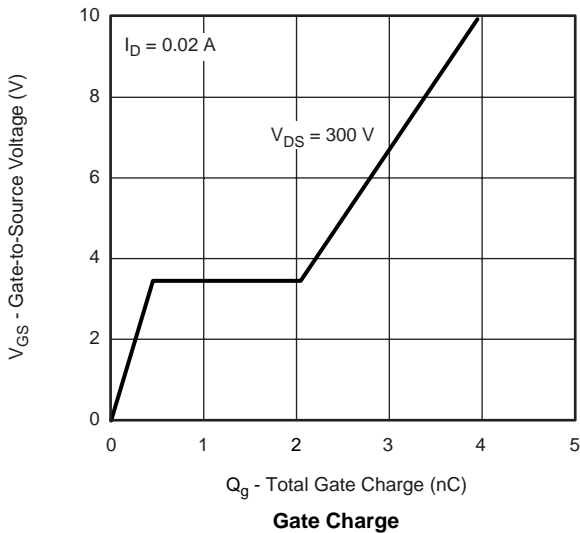
Transfer Characteristics



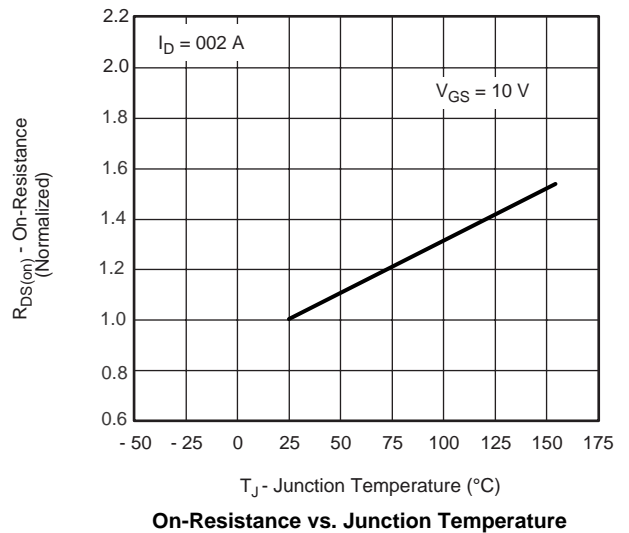
On-Resistance vs. Drain Current



Capacitance

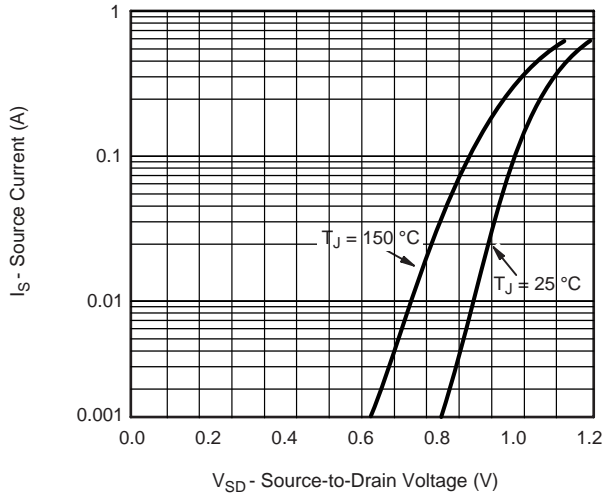


Gate Charge

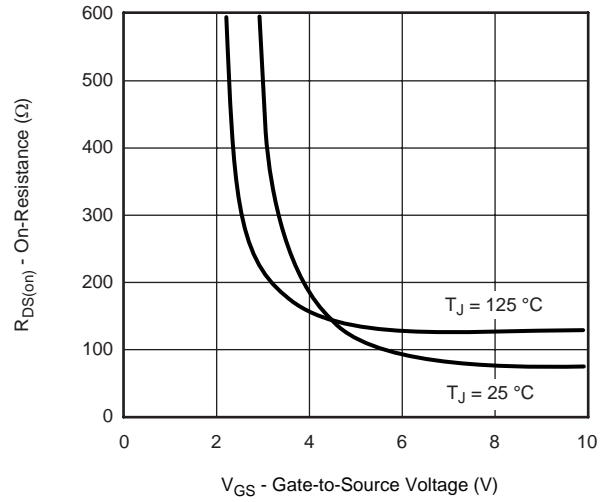


On-Resistance vs. Junction Temperature

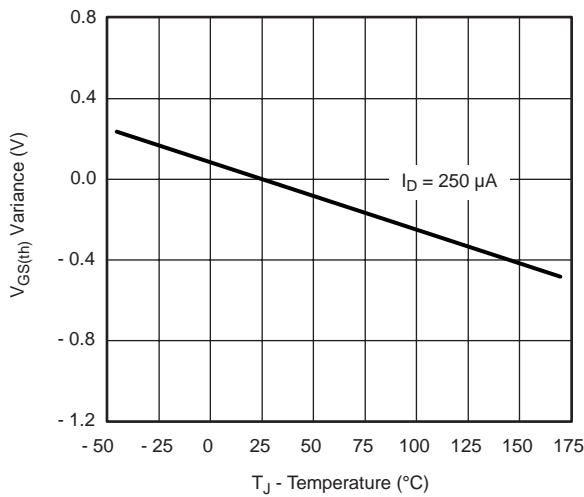
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



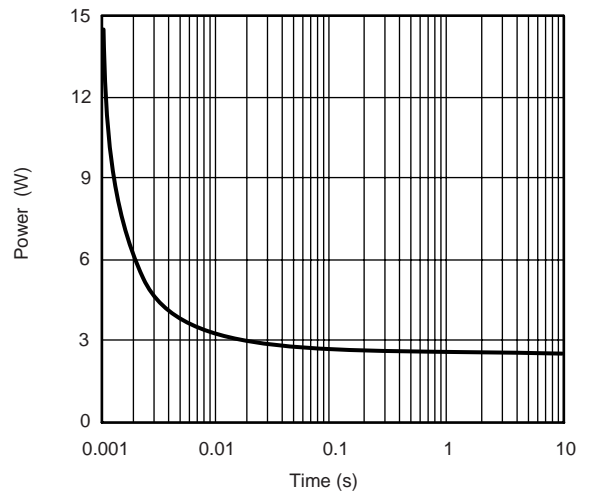
Source-Drain Diode Forward Voltage



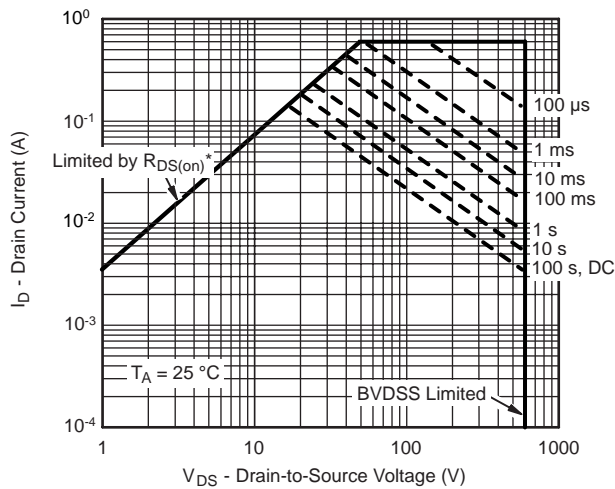
On-Resistance vs. Gate-to-Source Voltage



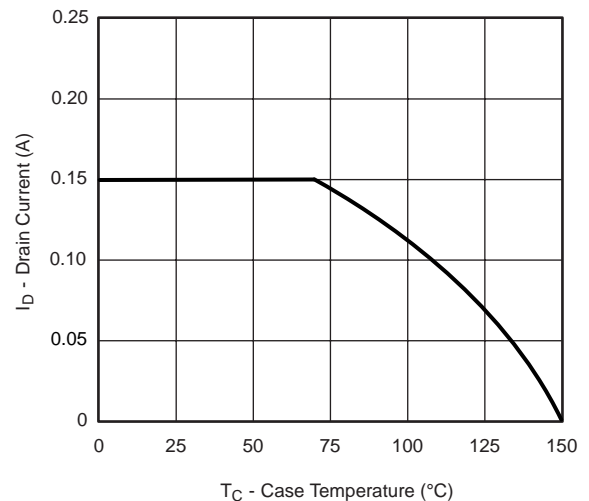
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

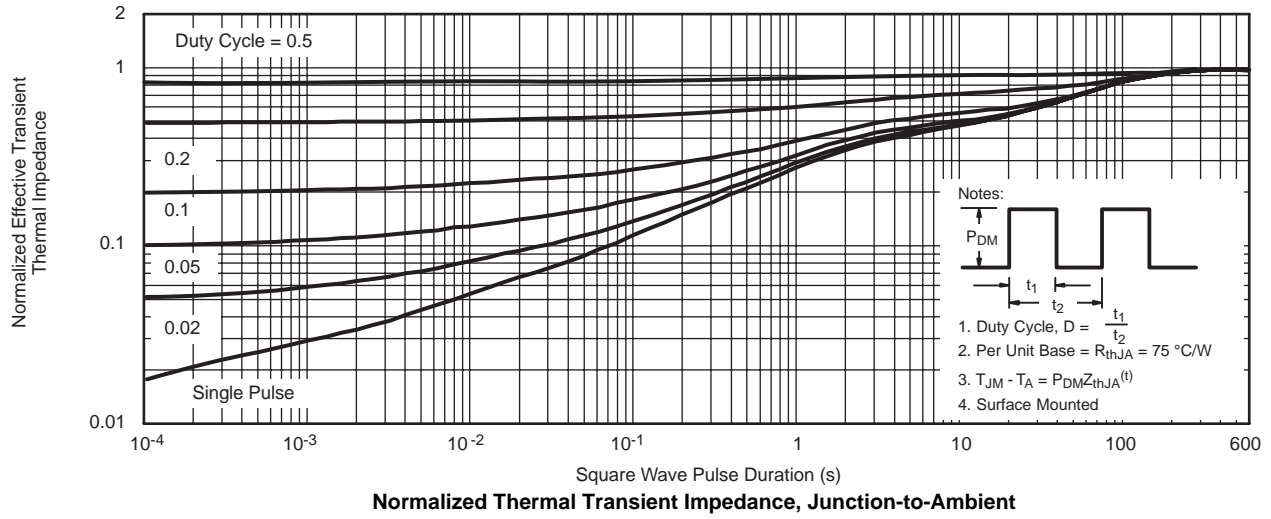


Safe Operating Area, Junction-to-Ambient



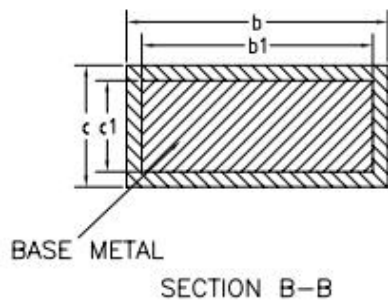
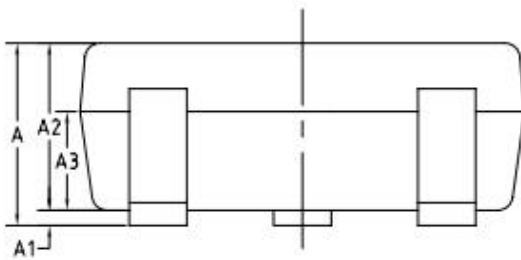
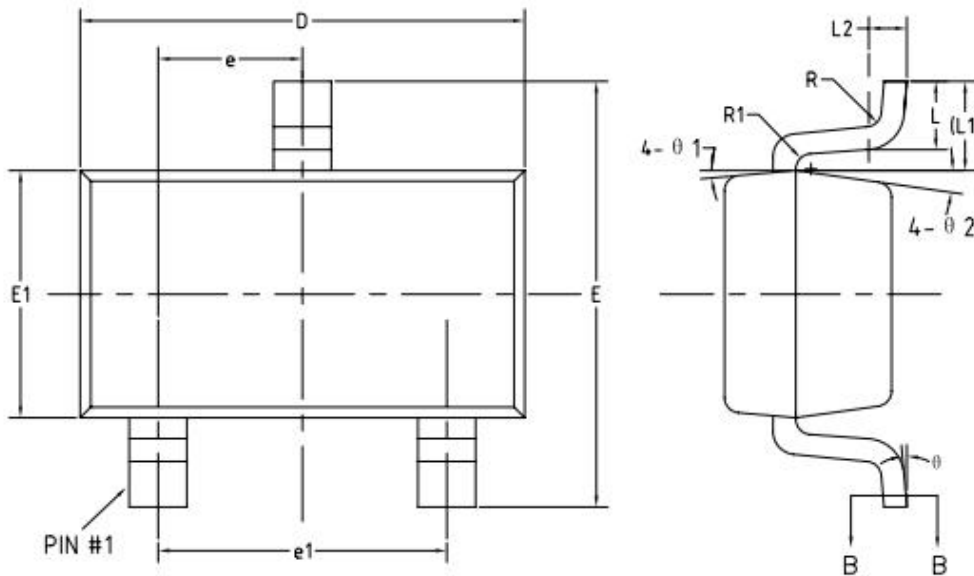
Current Derating*

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150 \text{ }^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

SOT-23-3L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	-	-	1.50
A1	0.00	-	0.18
A2	0.85	1.10	1.35
A3	0.58	0.65	0.72
b	0.23	-	0.53
b1	0.20	0.40	0.50
c	0.09	-	0.22
c1	0.08	0.13	0.21
D	2.78	2.95	3.10
E	2.58	2.80	3.03
E1	1.55	1.65	1.78
e	0.83	0.95	1.07
e1	1.78	1.90	2.02
L	0.28	0.45	0.62
L1	0.59REF		
L2	0.25BSC		
R	0.04	-	-
R1	0.04	-	0.21
θ	0°	-	8°
θ 1	8°	10°	12°
θ 2	8°	10°	12°

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